

Development of non-invasive micron beam size diagnostics using optical diffraction radiation

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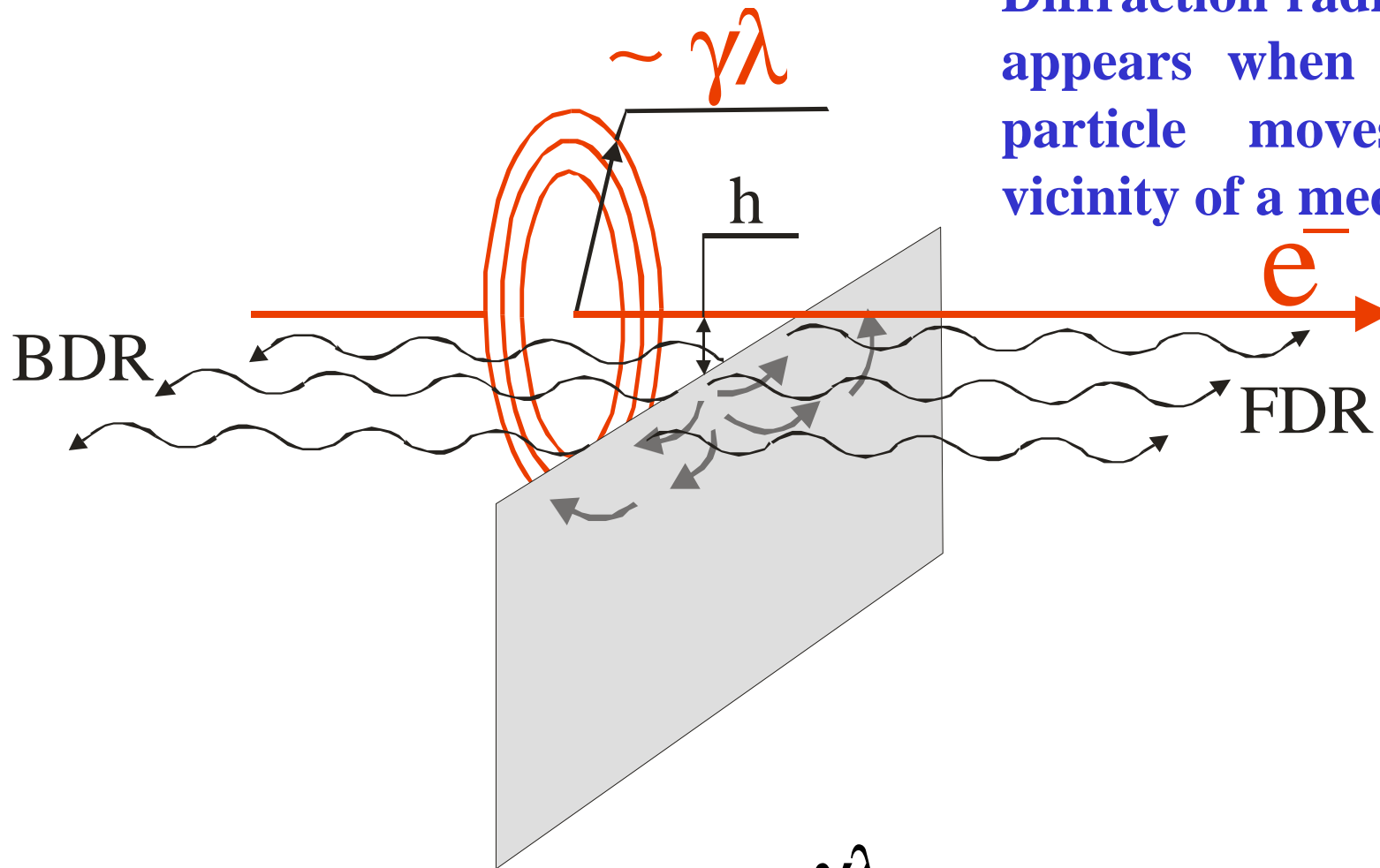
R. Hamatsu

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- Introduction
- Experimental setup
- Beam size measurement with ODR from a flat slit
- ODR interference for micron beam size measurements
- Summary

Diffraction Radiation production

Diffraction radiation (DR) appears when a charged particle moves in the vicinity of a medium



Impact parameter, h , – the shortest distance between the target and the particle trajectory

$$h \leq \frac{\gamma\lambda}{2\pi}$$

λ - observation wavelength

g - particle Lorentz-factor

BDIR

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Advantages of ODR technique

- **Non-invasive method**

(no beam perturbation or target destruction)

- **Instantaneous emission**

(quick measurements)

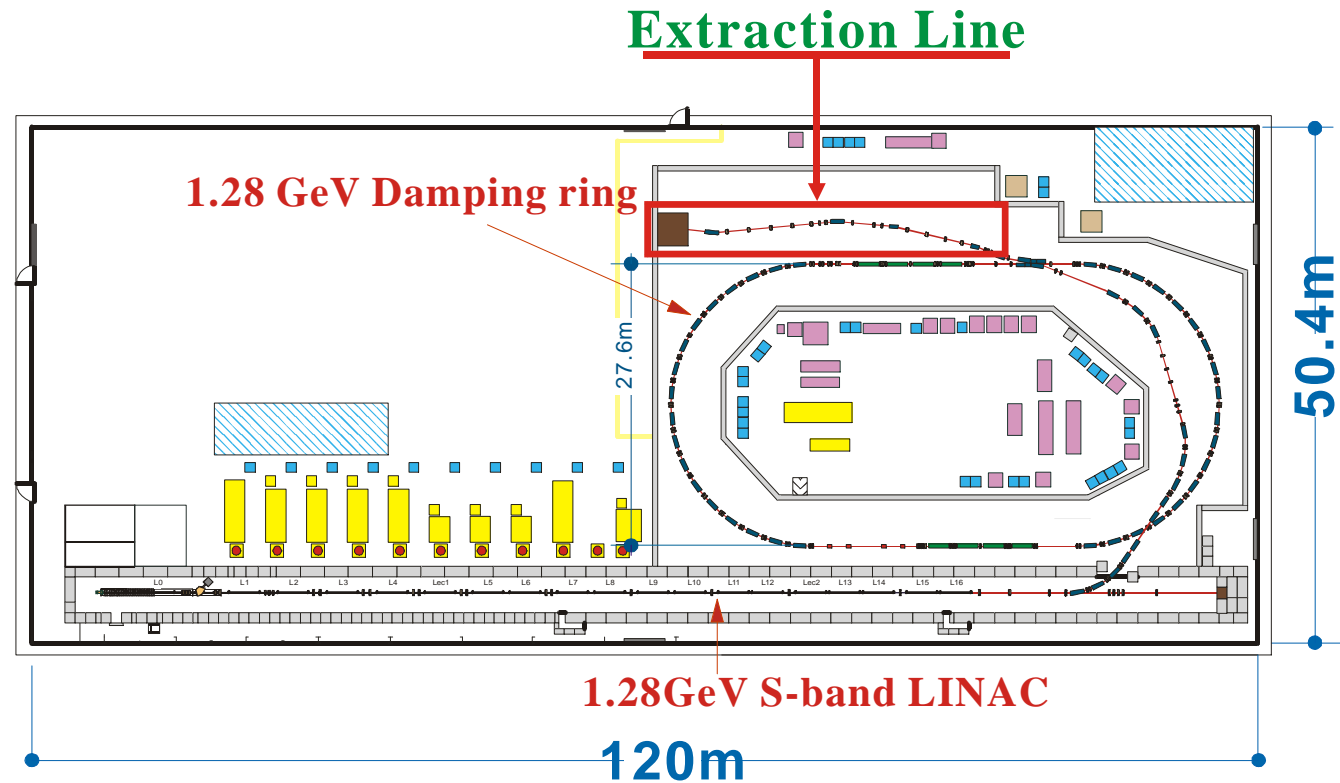
- **Single shot acquisition**

(no additional error from shot-by-shot instabilities)

- **~1-2m resolution is achievable**

(Linear collider goal – 10mm beam size with 1m resolution)

KEK – Accelerator Test Facility



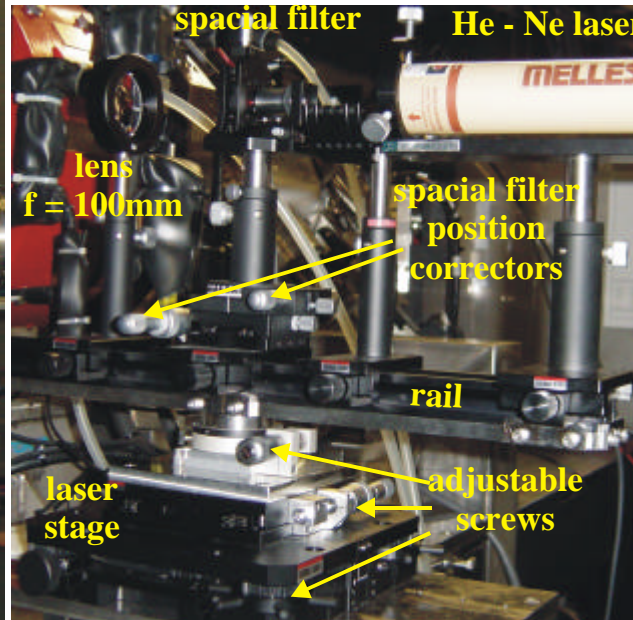
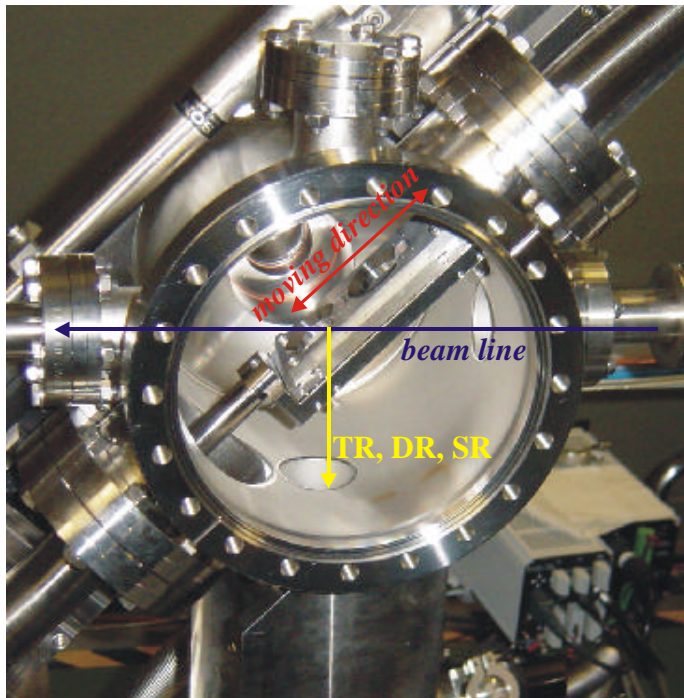
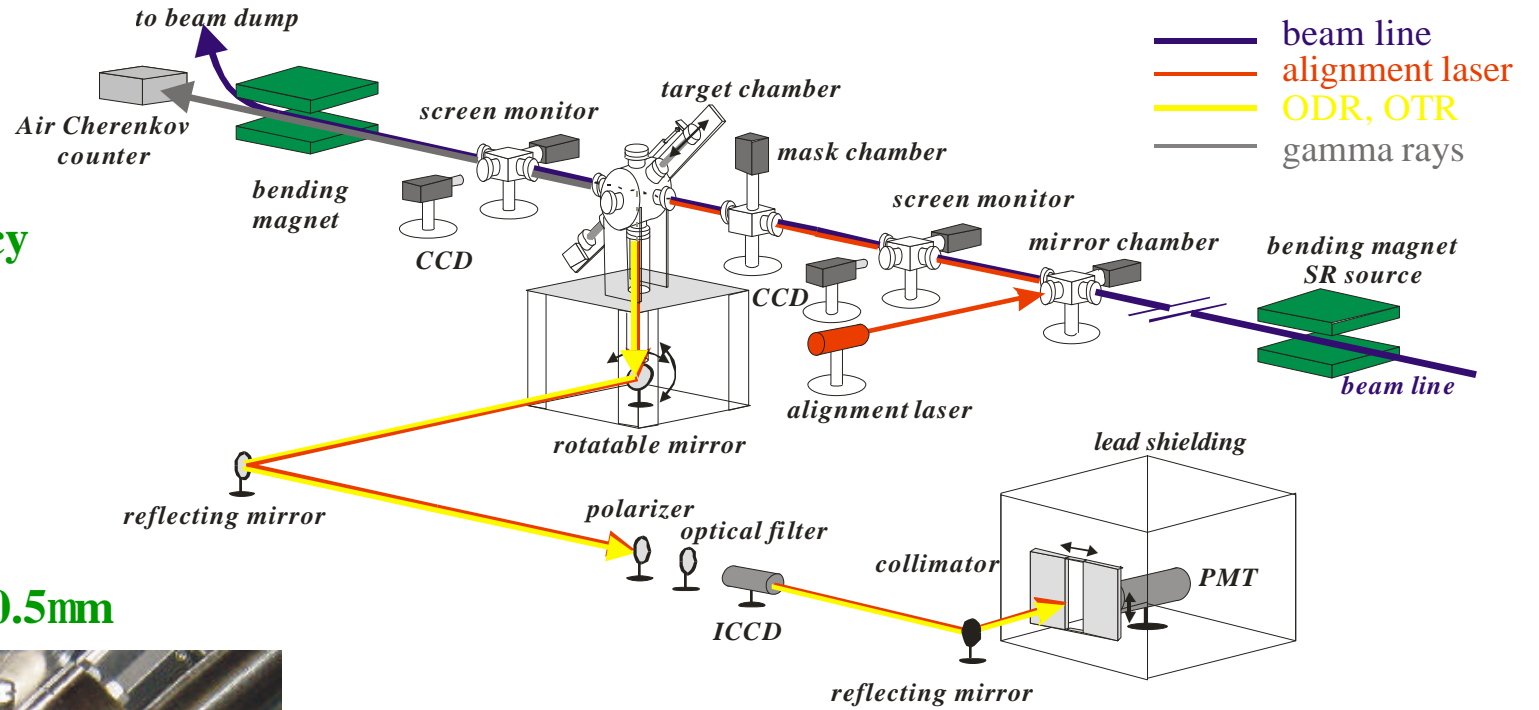
Electron beam parameters

Maximum energy		1.28 GeV ($g = 2500$)
Beam emittance	Vertical	$(1.5 \pm 0.25) \cdot 10^{-11}$ m rad
	Horizontal	$(1.4 \pm 0.3) \cdot 10^{-9}$ m rad
Vertical beam size (near the ODR target)		$S_y < 10\mu\text{m}$
Horizontal beam size (near the ODR target)		$S_x < 100\mu\text{m}$
Bunch length		~ 8 mm
Single-bunch population		$1.2 \cdot 10^{10}$
Energy spread		0.08%

Experimental layout

Alignment accuracy
 $< g^{-1} = 0.4\text{mrad}$

Linear gauge $< 0.5\text{mm}$



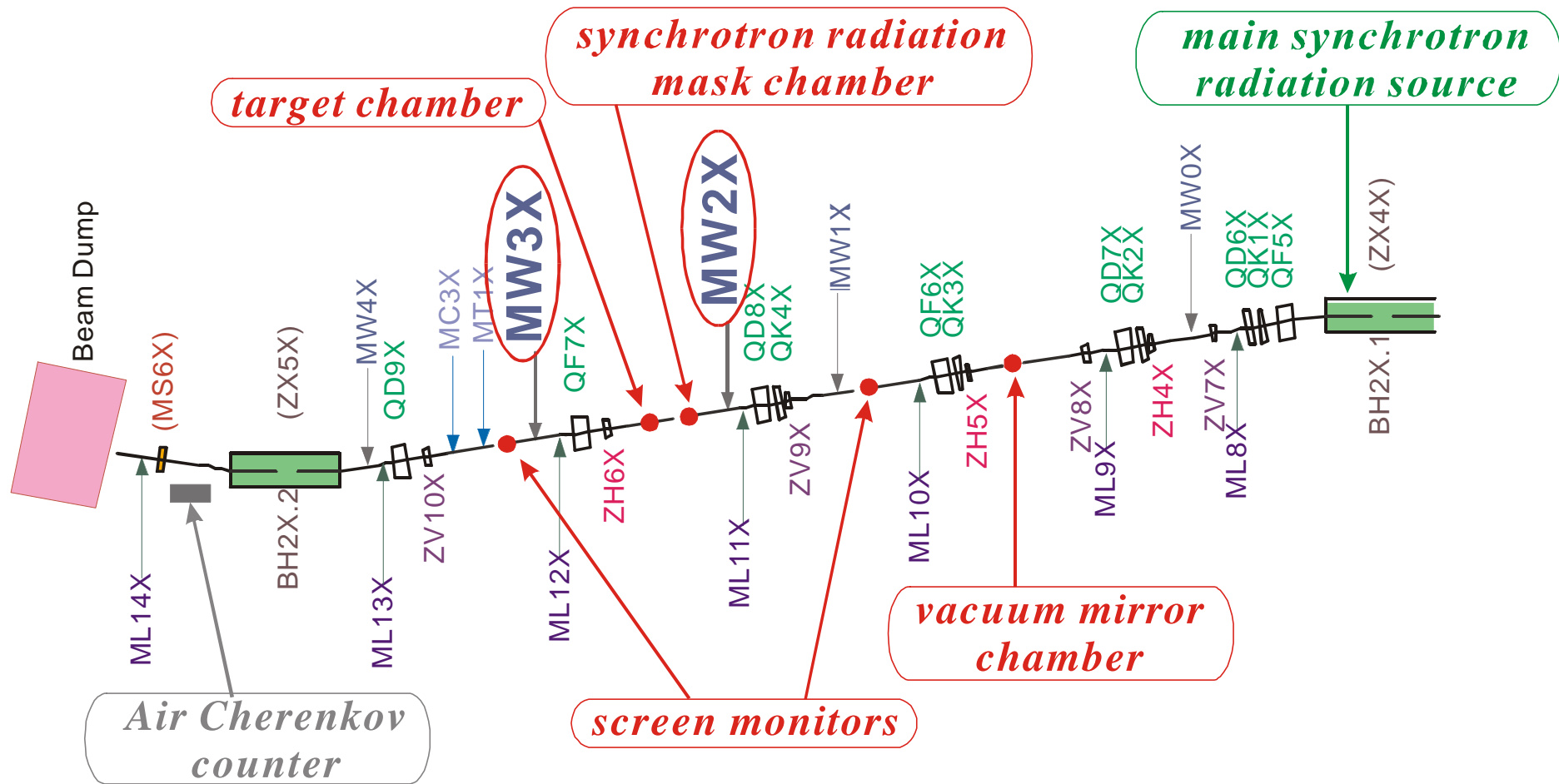
PMT (Hamamatsu H1161)
 spectral response range
 $\sim 300 - 650\text{nm}$

CCD (JAI corp. CV-M10)

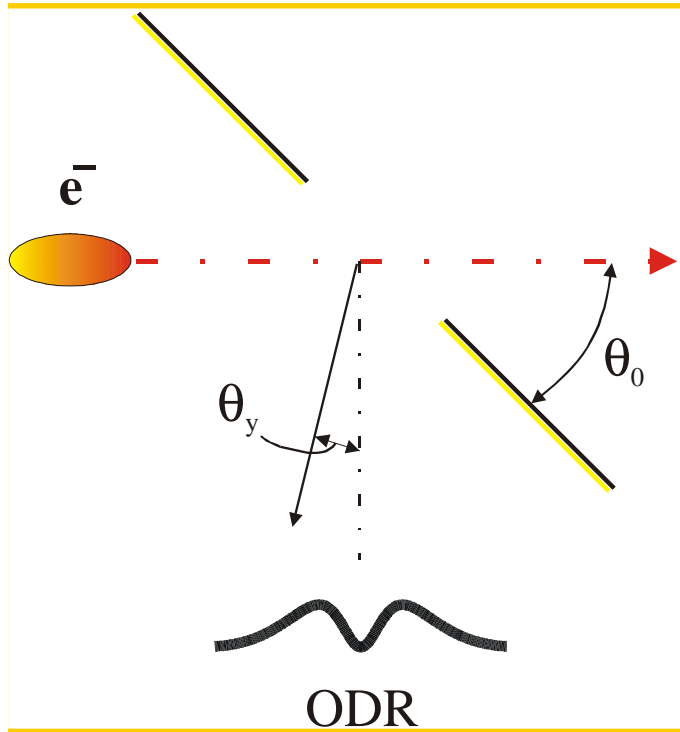
I.I. (Hamamatsu C4078-01)

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Extraction line layout



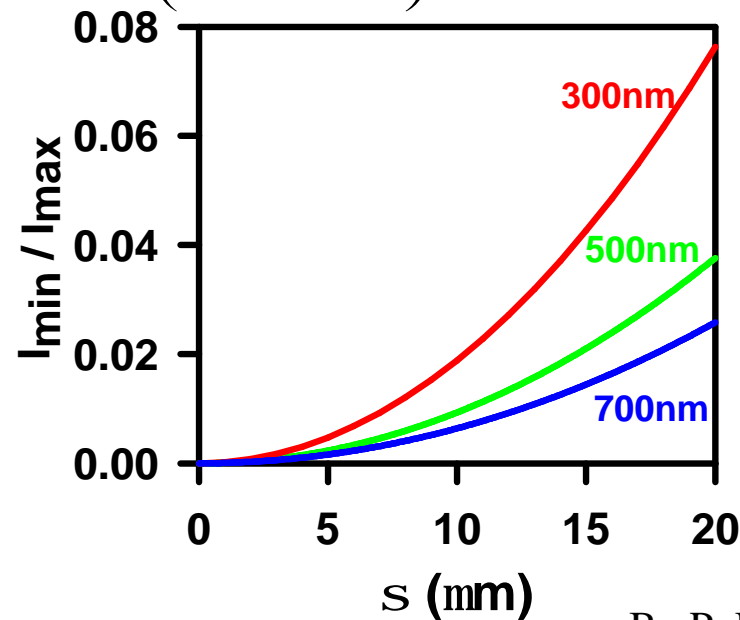
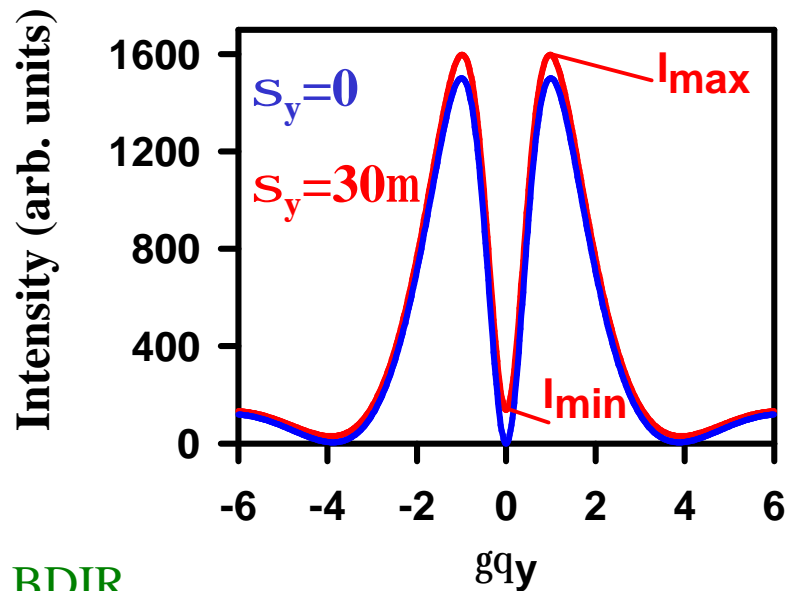
Beam size measurement using ODR from a flat slit



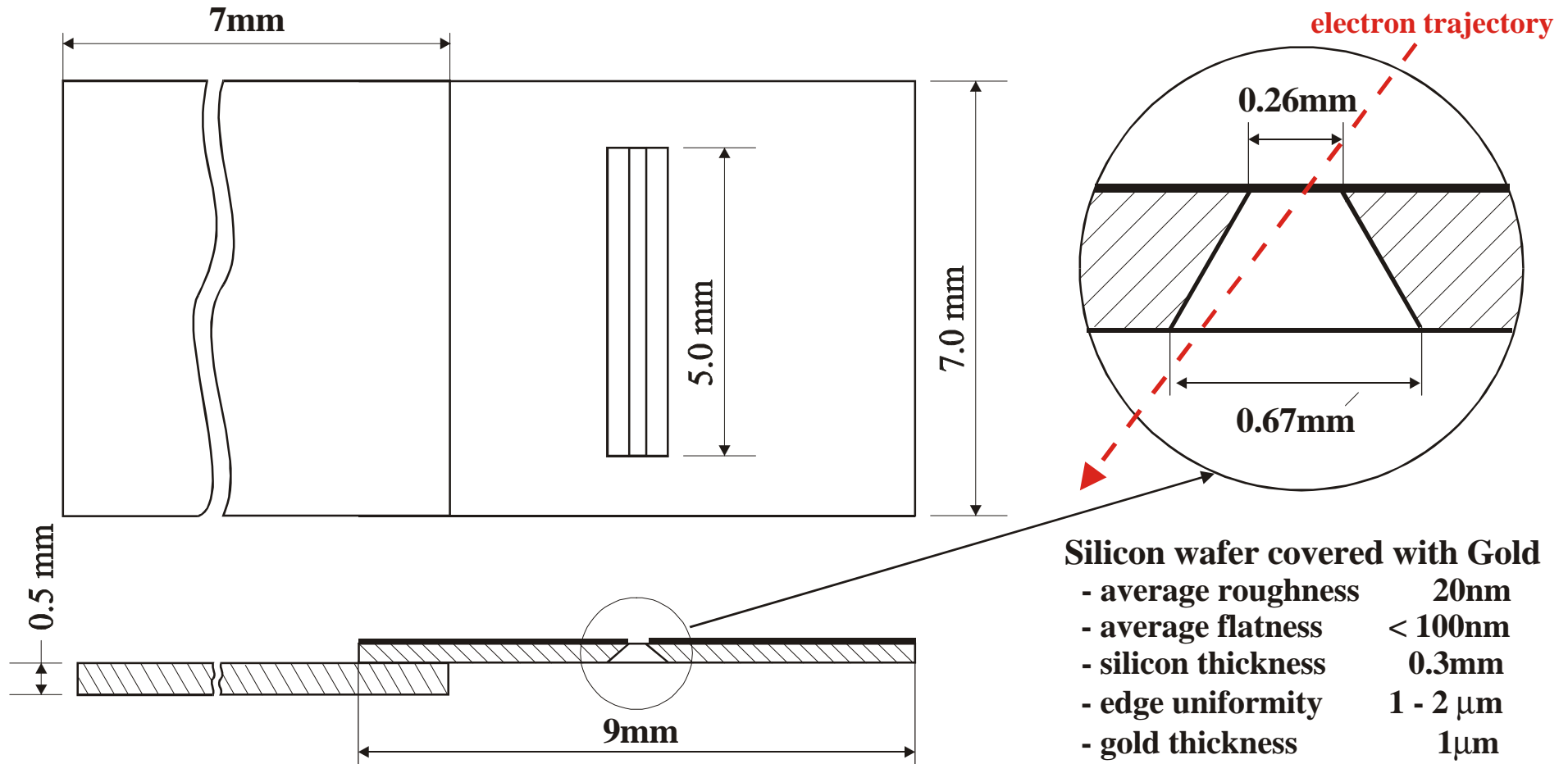
$$\frac{d^2 W_y^{\text{slit}}}{d\omega d\Omega} = \frac{\alpha |R_y|^2}{4\pi^2} \frac{\exp\left(-\frac{2\pi a_{\text{in}} \sin \theta_0}{\lambda} \sqrt{\gamma^{-2} + \theta_x^2}\right)}{\gamma^{-2} + \theta_x^2 + \theta_y^2} \times$$

$$\left\{ \exp\left[\frac{8\pi^2 \sigma_y^2}{\lambda^2} (\gamma^{-2} + \theta_x^2)\right] - \cos\left[\frac{2\pi a \sin \theta_0}{\lambda} \theta_y + 2\psi\right] \right\}$$

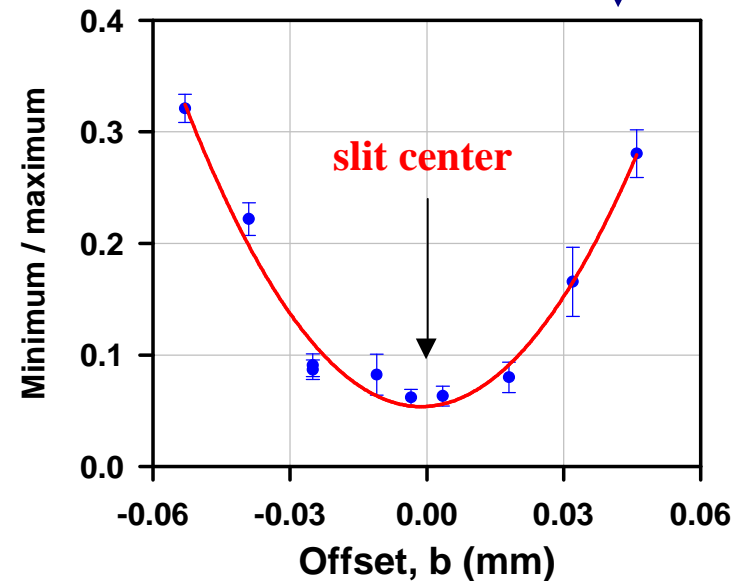
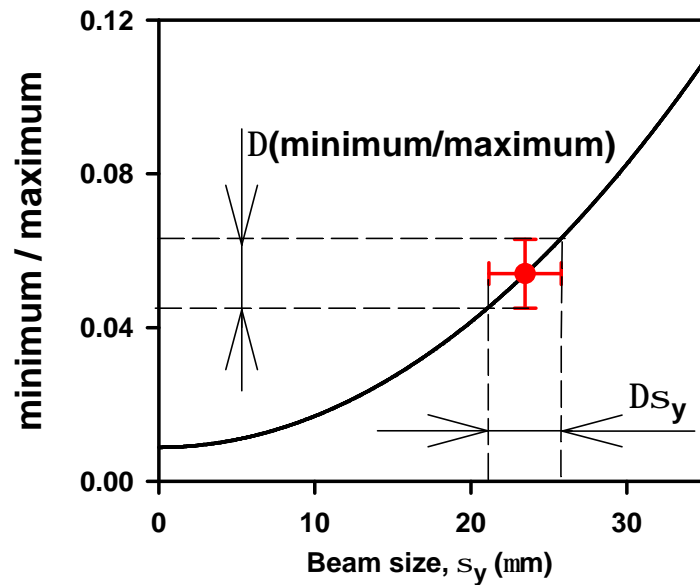
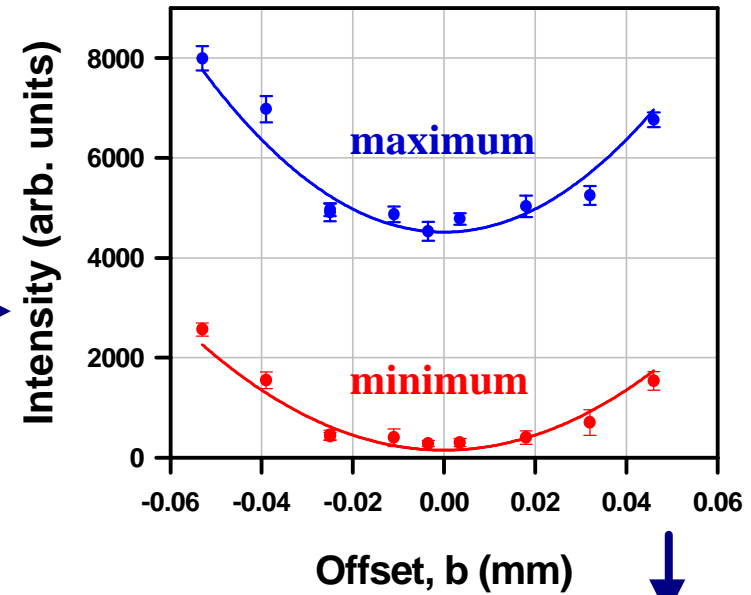
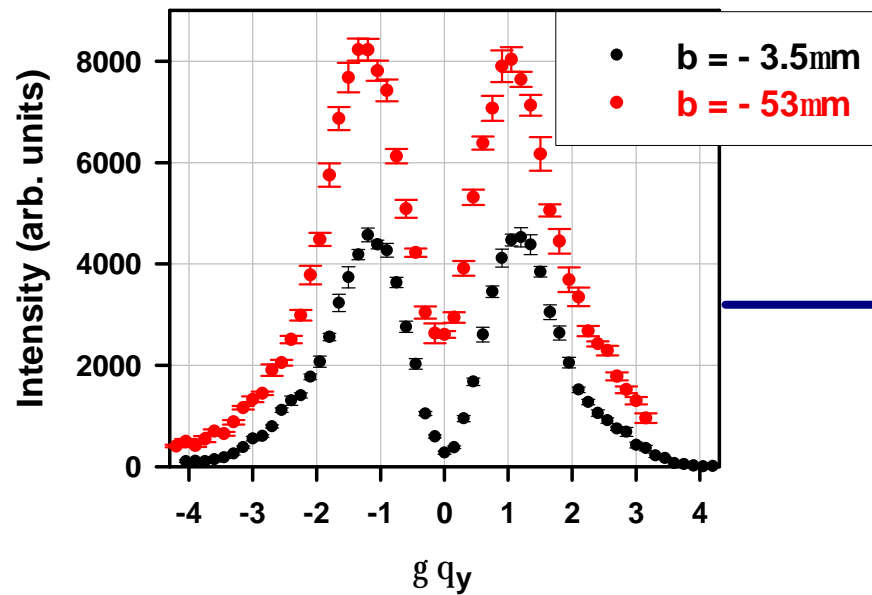
$$\psi = \arctan\left(\frac{\theta_y}{\sqrt{\gamma^{-2} + \theta_x^2}}\right)$$



Target – silicon wafer covered with gold

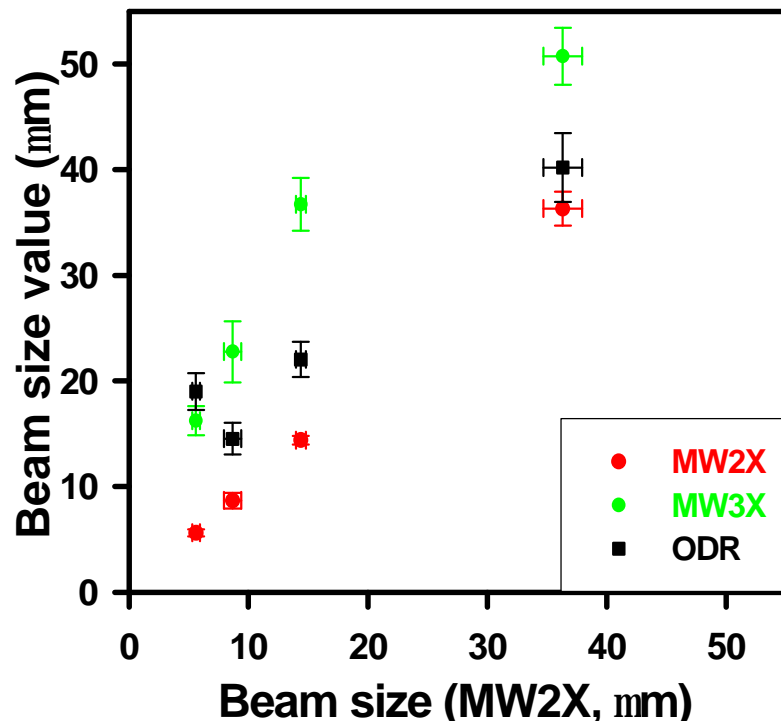


Method for the beam size measurement

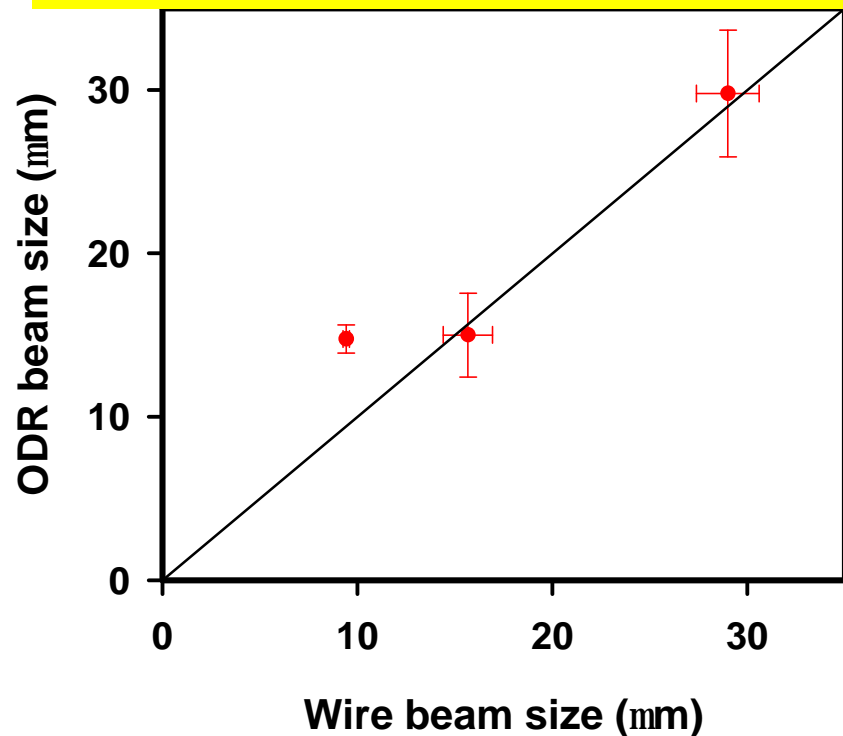


Beam size measurement

Correlation between the ODR (black points) and two wire scanners installed upstream (red points) and downstream (green points) the target.



Correlation between the the ODR and the beam size measured with 10mm tungsten wire installed in the target chamber at the same position as the target. The black line represents a 45 degree line.

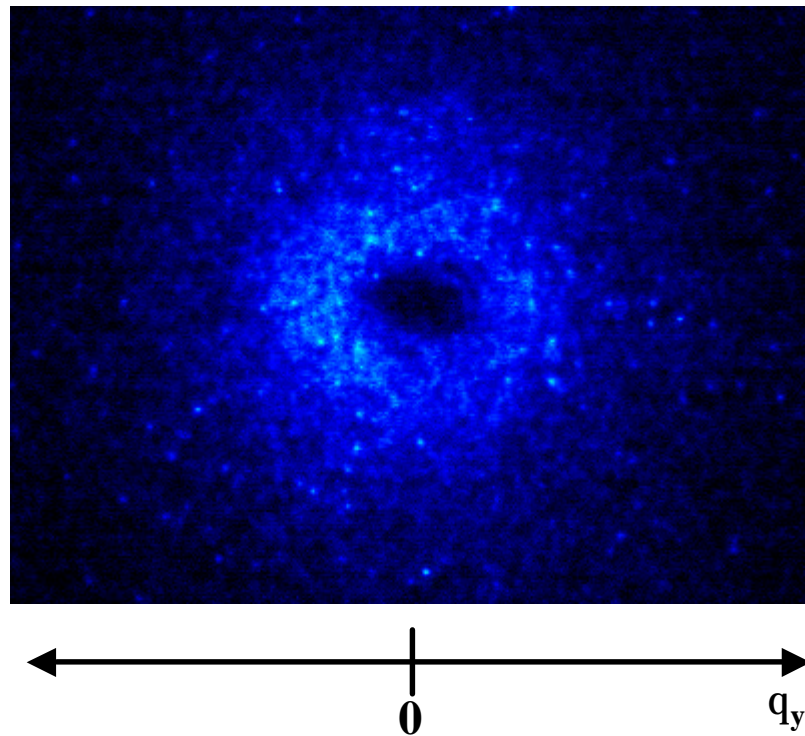


$$z = \frac{2\pi a_{in}}{\gamma\lambda} \geq 1; \quad 1 \gg \frac{\sigma}{a_{in}} > 0.01$$

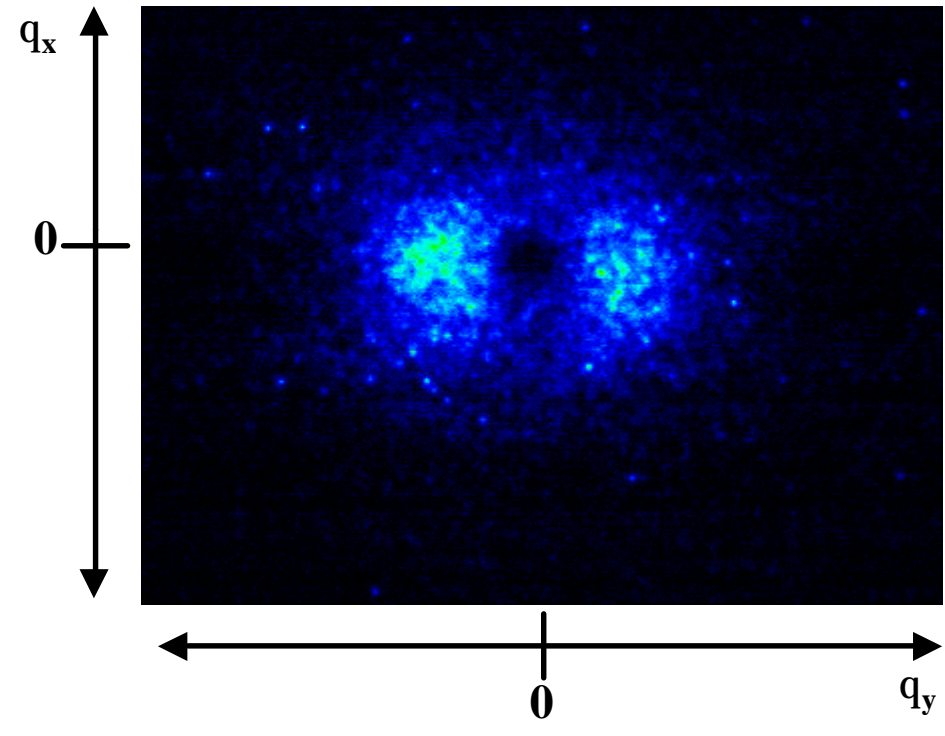
Limitation

Single shot OTR and ODR measurement without the polarizer

OTR

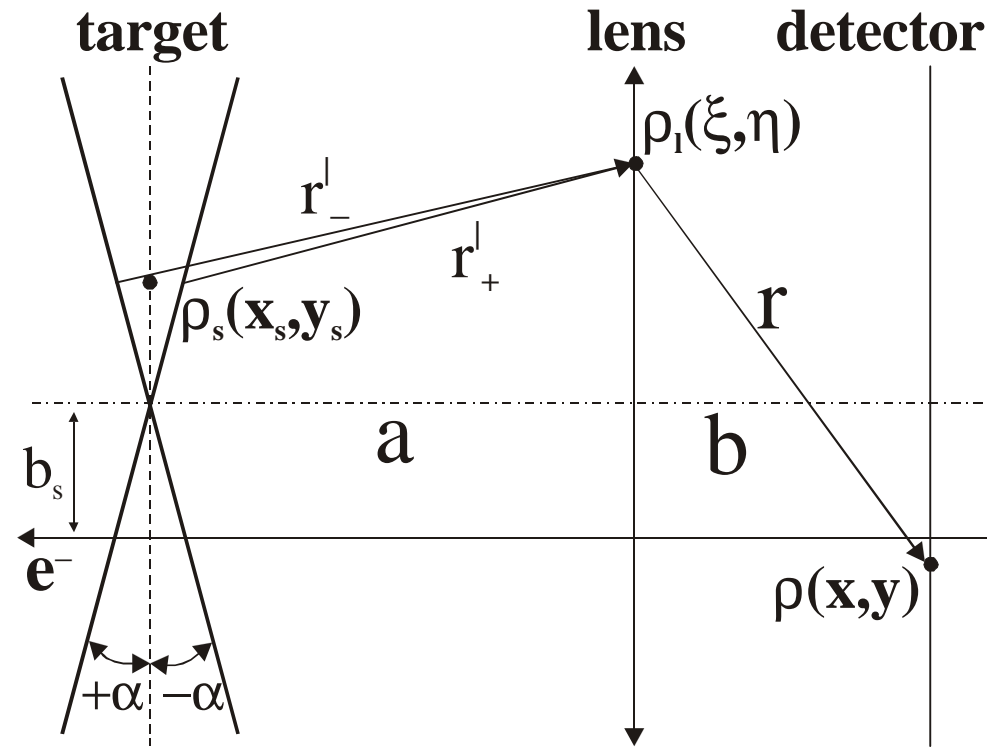
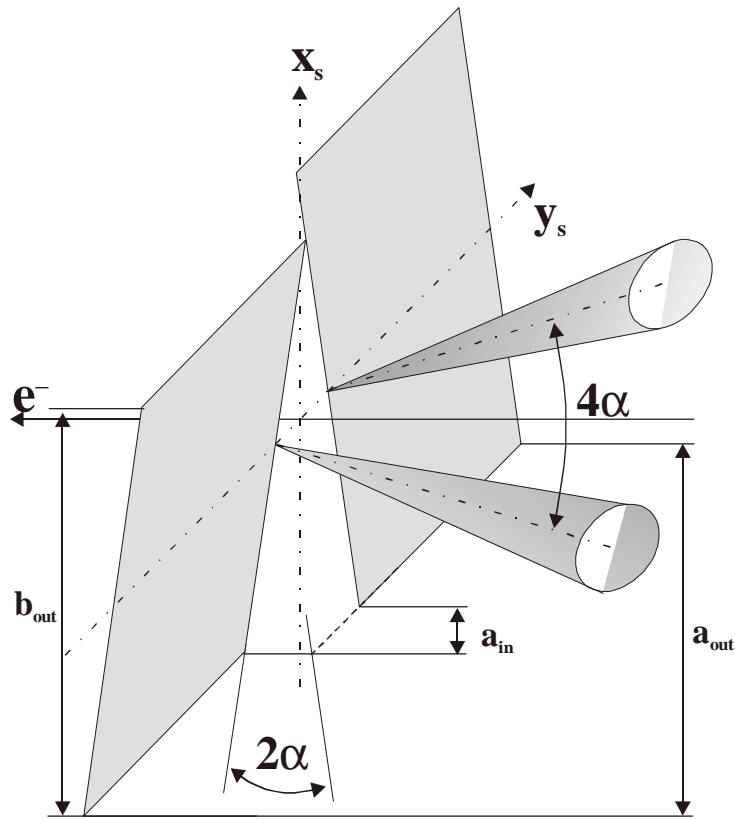


ODR



Optical filter $\lambda = 550 \pm 20 \text{nm}$

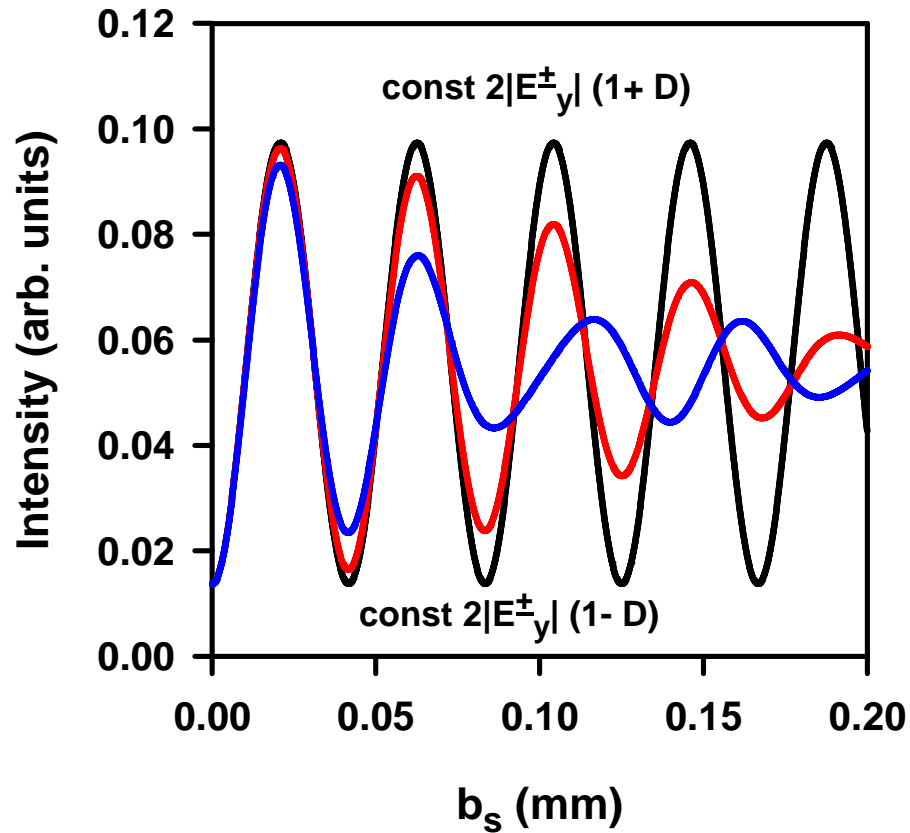
ODR Interference for micron beam size diagnostics



$$I_y = \left| E_y^+ \right|^2 + \left| E_y^- \right|^2 + 2 \left| E_y^+ \right| \left| E_y^- \right| \cos \left(\psi_+ - \psi_- + 4k\alpha \left(b_s - \frac{x}{m} \right) \right) D$$

$$\begin{Bmatrix} E_y^{(R)\pm} \\ E_y^{(I)\pm} \end{Bmatrix} = \left| E_y^\pm \right| \cdot \begin{Bmatrix} \cos(\psi_\pm) \\ \sin(\psi_\pm) \end{Bmatrix}, \quad \text{where} \quad \psi_\pm = \tan^{-1} \left[\frac{E_y^{(I)\pm}}{E_y^{(R)\pm}} \right]$$

Dependence of the ODR intensity vs. target position



$$D = \int_{-\infty}^{\infty} \text{Gauss}(\sigma_x, \Delta b_s) e^{i4k\alpha\Delta b_s} d\Delta b_s$$

$$= \exp[-8k^2\alpha^2\sigma_x^2]$$

Visibility

$$V = \frac{I_{\max} - I_{\min}}{I_{\max} + I_{\min}} = D$$

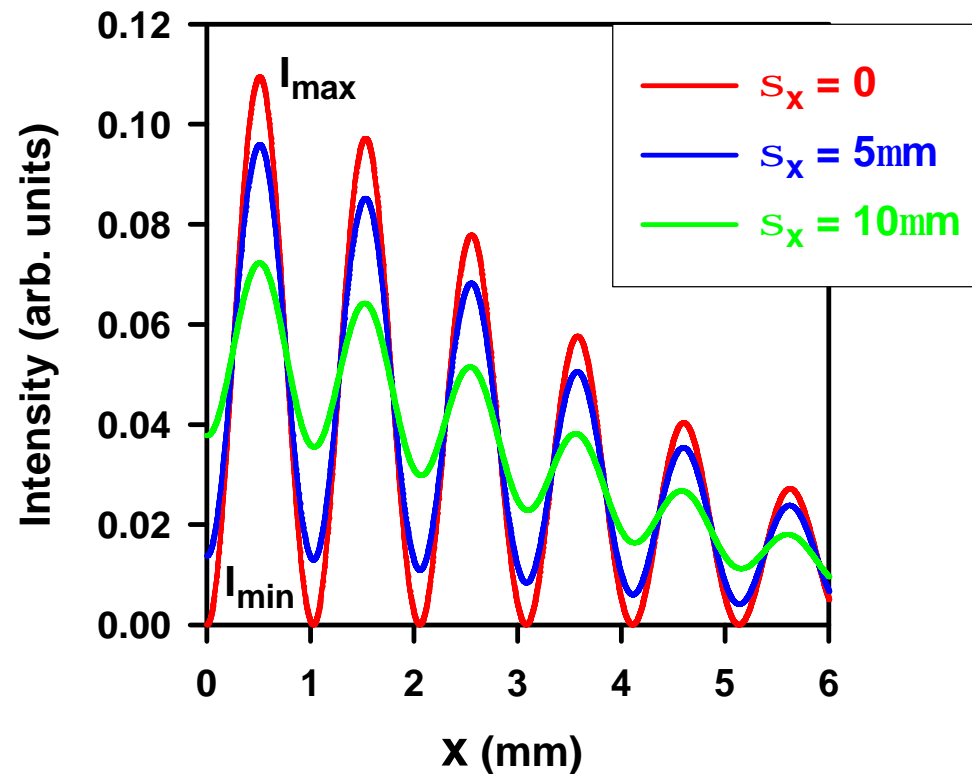
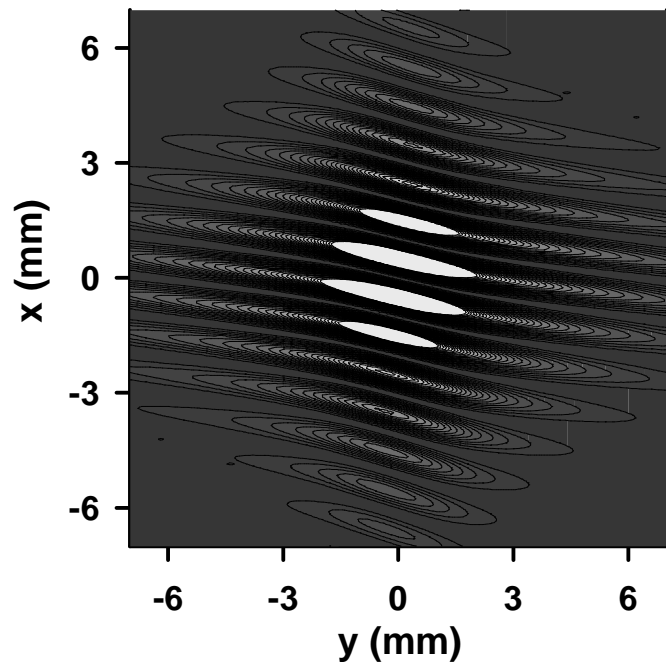
Black line – differential intensity

Red line - D1 = 20%

Blue line - D1 = 40%

A method for the beam size measurement

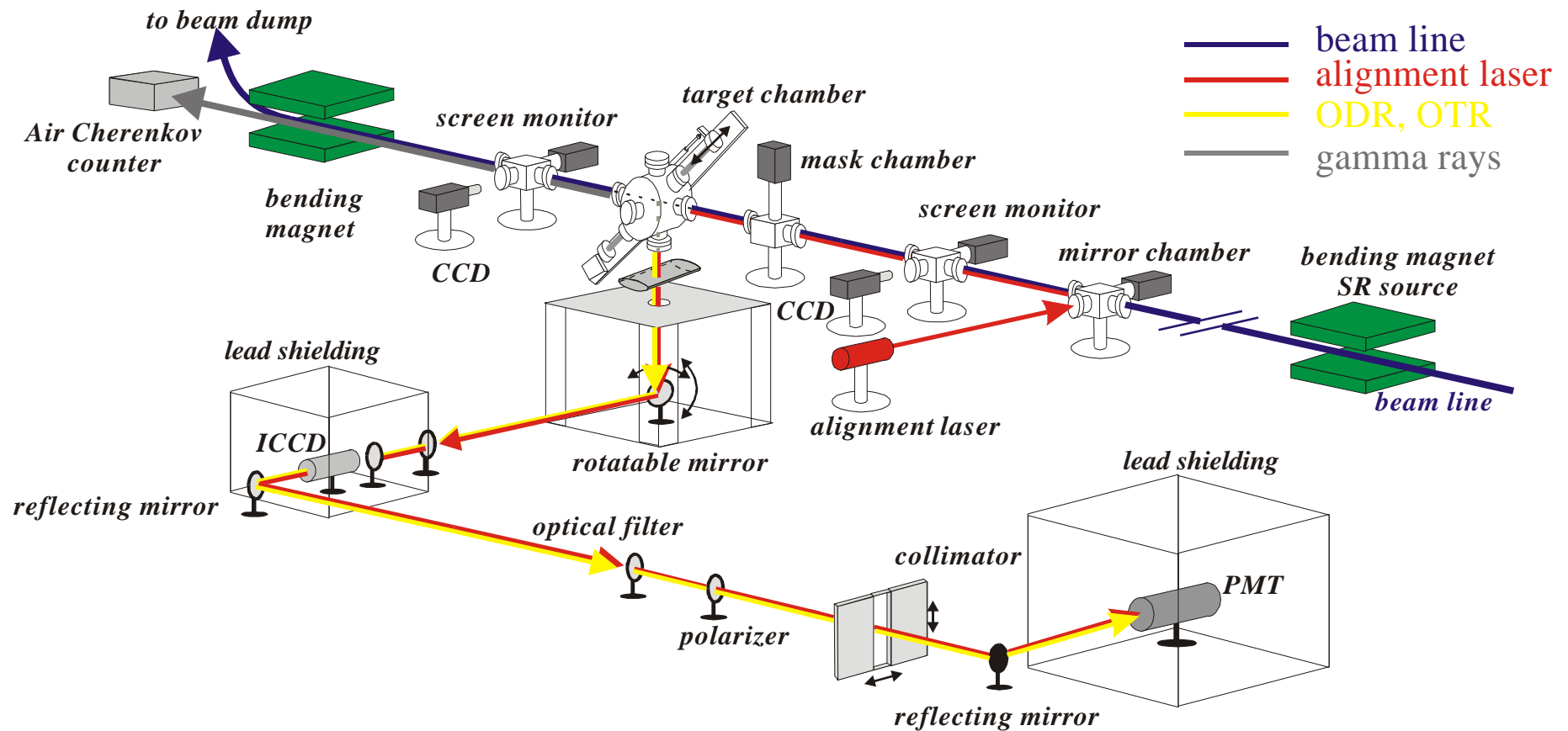
ODR interference pattern that could be observed with a CCD



$$\sigma_x = \frac{\lambda}{4\pi\alpha} \sqrt{\frac{\ln(V^{-1})}{2}}$$

$\lambda = 558\text{nm}$ - observation wavelength;
 $2\alpha = 6.2\text{mrad}$ - angle between two target plates

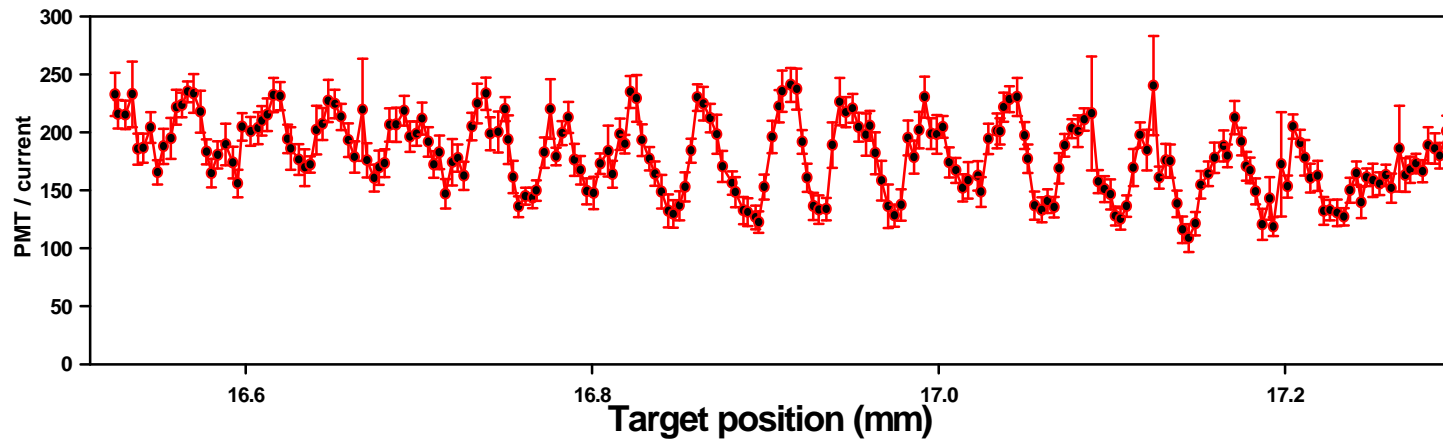
Modified experimental layout



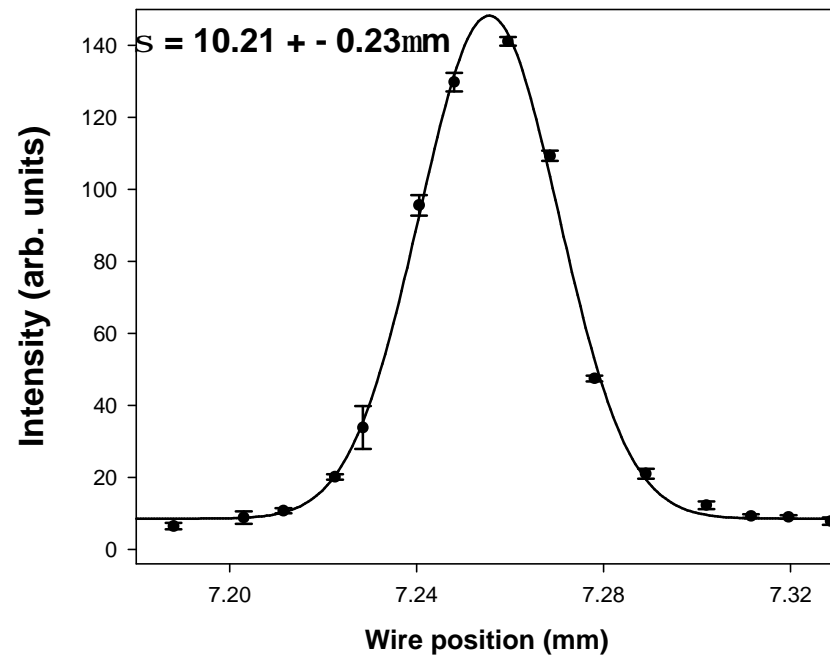
Target to ICCD distance = 1.9m
 Lens $f = 150\text{mm}$

Target parameters: $2\alpha = 6.2\text{mrad}$
 $a_{\text{in}} = 420\mu\text{m}$

Measurements with photomultiplier



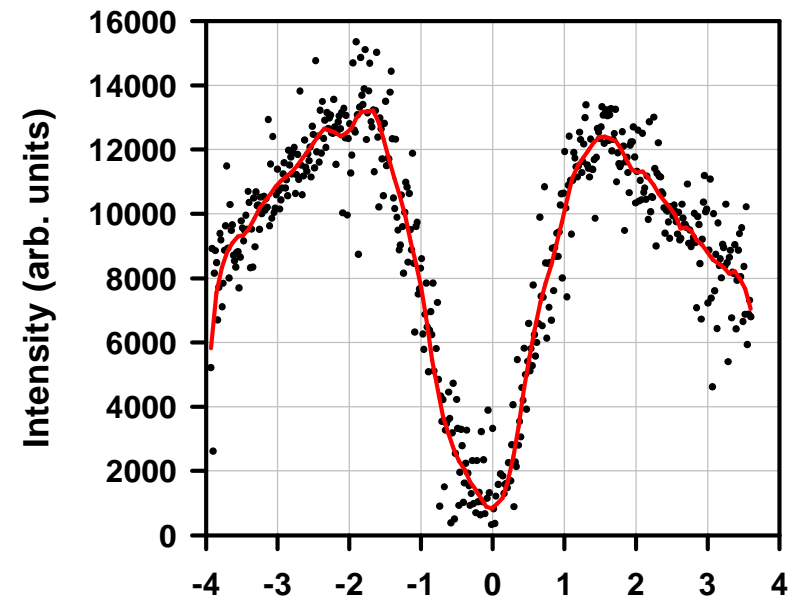
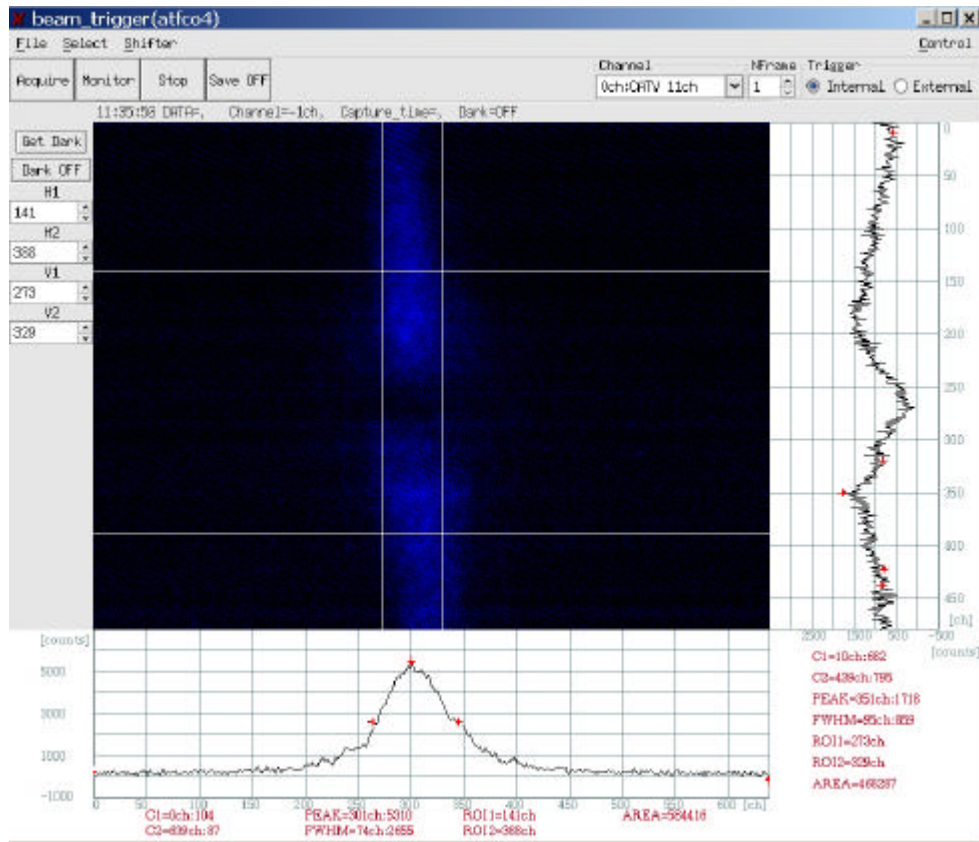
$$\text{Period} = \frac{\lambda}{2\alpha} = 45\mu\text{m}$$



Estimated beam size:

$$\sigma = \frac{\lambda}{4\pi\alpha} \sqrt{\frac{\ln(V^{-1})}{2}} = 11.4 \pm 1.2\mu\text{m}$$

Measurements of OTR with ICCD

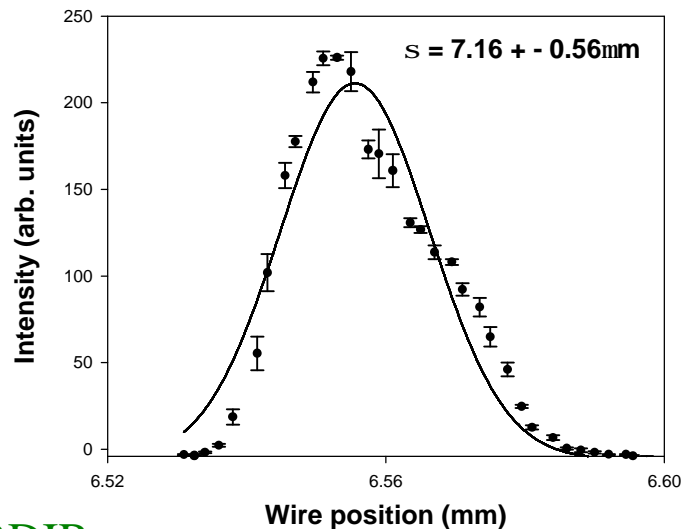
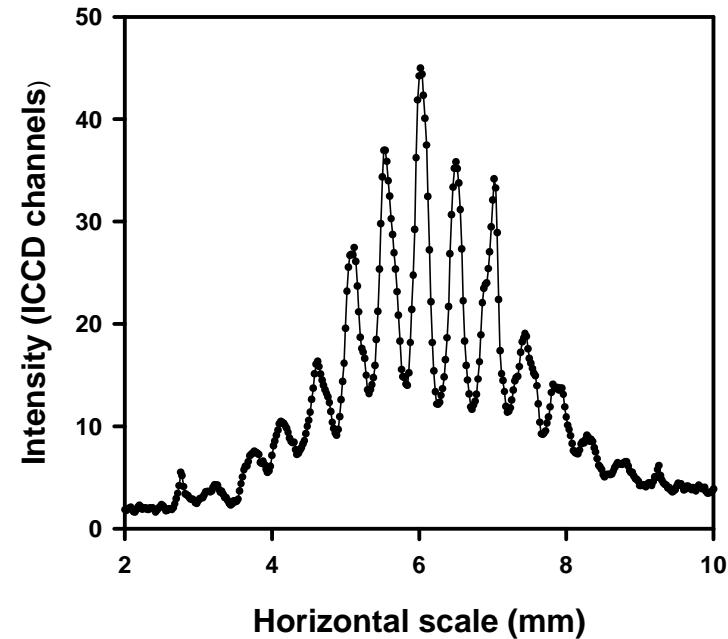
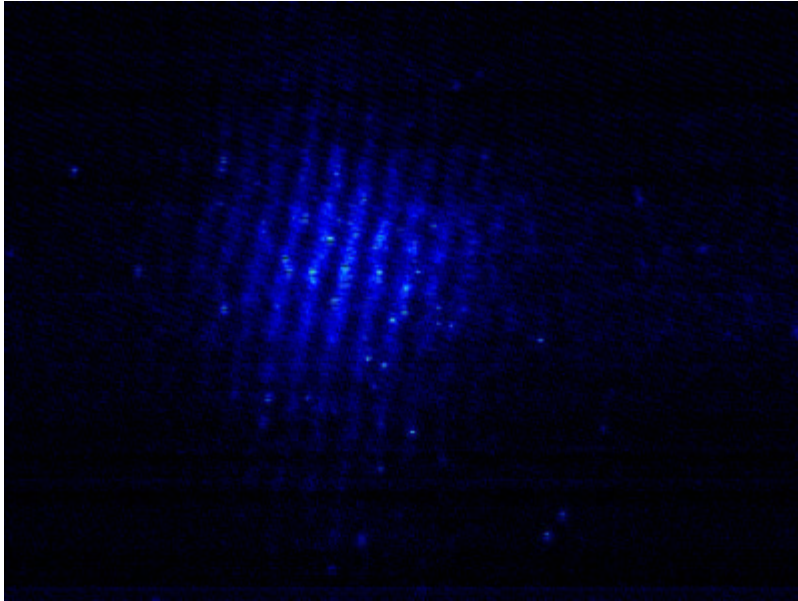


gq_x

Preliminary of ODR with ICCD

The beam current was increased to $5 \cdot 10^{10}$ e/pulse

Integrated over 100 channels of ICCD



Estimated beam size:

$$\sigma = \frac{\lambda}{4\pi\alpha} \sqrt{\frac{\ln(V^{-1})}{2}} = 6.2 \mu\text{m}$$

Summary

- a new method for micron beam size diagnostics using interference properties of diffraction radiation was developed and tested at the ATF extraction line
 - the periodic behavior of the ODR pattern as a function of the target position was confirmed
 - a single shot ODR measurements with ICCD was performed
 - the electron beam size was estimated and compared with the measurements with wire scanner
-
- the measurements require very high beam current $5 \cdot 10^{10}$
 - it is a promising technique for extremely high energy electrons like SLAC FFTB ($g = 60000$)

**Non-invasive micron high energy electron beam
size measurement using diffraction radiation
at SLAC FFTB**

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